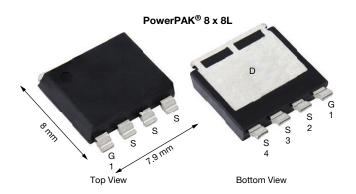


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# Automotive N-Channel 40 V (D-S) 175 °C MOSFET

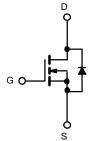


PRODUCT SUMMARY				
V <sub>DS</sub> (V)	40			
$R_{DS(on)}(\Omega)$ at $V_{GS} = 10 \text{ V}$	0.00124			
I <sub>D</sub> (A) <sup>e</sup>	345			
Configuration	Single			

#### **FEATURES**

- TrenchFET® Gen IV power MOSFET
- AEC-Q101 qualified
- 100 % Rq and UIS tested
- Thin 1.6 mm package
- · Very low thermal resistance
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912





N-Channel MOSFET

ORDERING INFORMATION	
Package	PowerPAK 8 x 8L
Lead (Pb)-free and halogen-free	SQJQ142E (for detailed order number please see <a href="https://www.vishay.com/doc?79776">www.vishay.com/doc?79776</a> )

<b>ABSOLUTE MAXIMUM RATIN</b>	<b>GS</b> ( $T_C = 25$ °C, unless	s otherwise noted	<u> </u>	
PARAMETER	SYMBOL	LIMIT	UNIT	
Drain-source voltage		V <sub>DS</sub>	40	V
Gate-source voltage		$V_{GS}$	V <sub>GS</sub> ± 20	
Continuous drain current <sup>e</sup>	T <sub>C</sub> = 25 °C	1	345	A
	T <sub>C</sub> = 125 °C	Ι <sub>D</sub>	199	
Continuous source current (diode conduct	ion) <sup>e</sup>	I <sub>S</sub>	252	
Pulsed drain current a, e		I <sub>DM</sub>	791	
Single pulse avalanche current	L = 0.1 mH	I <sub>AS</sub>	48	
Single pulse avalanche energy	L = 0.1 mn	E <sub>AS</sub>	115.2	mJ
Maximum power dissipation <sup>e</sup>	T <sub>C</sub> = 25 °C	D	277	10/
	T <sub>C</sub> = 125 °C	$P_{D}$	92	W
Operating junction and storage temperature range		T <sub>J</sub> , T <sub>stg</sub>	-55 to +175	°C
Soldering recommendations (peak temperature) c			260	C

THERMAL RESISTANCE RATINGS				
PARAMETER		SYMBOL	LIMIT	UNIT
Junction-to-ambient	PCB mount c	$R_{thJA}$	44	°C/W
Junction-to-case (drain) <sup>d</sup>		$R_{thJC}$	0.54	C/VV

#### Notes

- a. Pulse test; pulse width  $\leq$  300 µs, duty cycle  $\leq$  2 %
- b. When mounted on 1" square PCB (FR4 material)
- c. See solder profile (<a href="https://www.vishay.com/doc?73257">www.vishay.com/doc?73257</a>). The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection
- d. As per JESD51-14
- e. Values based on R<sub>thJC</sub> and T<sub>C</sub> of 25 °C. Actual values achievable will be dependent on the thermal characteristics of the complete system



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PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT	
Static								
Drain-source breakdown voltage	V <sub>DS</sub>	$V_{GS}$	= 0, I <sub>D</sub> = 250 μA	40	-	-	\/	
Gate-source threshold voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> =	- V <sub>GS</sub> , I <sub>D</sub> = 250 μA	2	3	3.5	· ·	
Gate-source leakage	I <sub>GSS</sub>	V <sub>DS</sub> =	0 V, V <sub>GS</sub> = ± 20 V	-	-	± 100	nA	
		$V_{GS} = 0 V$	V <sub>DS</sub> = 40 V	-	-	1		
Zero gate voltage drain current	I <sub>DSS</sub>	$V_{GS} = 0 V$	$V_{DS} = 40 \text{ V}, T_{J} = 125 ^{\circ}\text{C}$	-	-	200	μΑ	
		$V_{GS} = 0 V$	V <sub>DS</sub> = 40 V, T <sub>J</sub> = 175 °C	-	-	330		
On-state drain current <sup>a</sup>	I <sub>D(on)</sub>	V <sub>GS</sub> = 10 V	$V_{DS} \ge 5 V$	100	-	-	Α	
		V <sub>GS</sub> = 10 V	I <sub>D</sub> = 20 A	-	0.00100	0.00124		
Drain-source on-state resistance a	R <sub>DS(on)</sub>	V <sub>GS</sub> = 10 V	I <sub>D</sub> = 20 A, T <sub>J</sub> = 125 °C	-	-	0.00200	ν nA μA Ω Ω Ω Ω Ω ης	Ω
		V <sub>GS</sub> = 10 V	I <sub>D</sub> = 20 A, T <sub>J</sub> = 175 °C	-	-	0.00240		
Forward transconductance b	9 <sub>fs</sub>	$V_{DS}$	= 15 V, I <sub>D</sub> = 60 A	-	150	-	S	
Dynamic <sup>b</sup>								
Input capacitance	C <sub>iss</sub>			-	5360	6975		
Output capacitance	C <sub>oss</sub>	$V_{GS} = 0 V$	$V_{DS} = 25 \text{ V}, f = 1 \text{ MHz}$	-	2070	2700	pF	
Reverse transfer capacitance	C <sub>rss</sub>			-	167	215		
Total gate charge <sup>c</sup>	Qg			-	92	130		
Gate-source charge c	Q <sub>gs</sub>	$V_{GS} = 10 \text{ V}$	$V_{DS} = 20 \text{ V}, I_{D} = 20 \text{ A}$	-	26	-	nC	
Gate-drain charge <sup>c</sup>	Q <sub>gd</sub>			-	20.1	=.		
Gate resistance	$R_g$		f = 1 MHz	0.65	1.59	2.56	Ω	
Turn-on delay time <sup>c</sup>	t <sub>d(on)</sub>			-	18.5	26		
Rise time <sup>c</sup>	t <sub>r</sub>	$V_{DD}$	= 20 V, $R_L = 1 \Omega$	-	18	25	ns ns	
Turn-off delay time <sup>c</sup>	t <sub>d(off)</sub>	$I_D \cong 20 A$ ,	$V_{GEN} = 10 \text{ V}, R_g = 1 \Omega$	-	37	52		
Fall time <sup>c</sup>	t <sub>f</sub>			-	14	20		
Source-Drain Diode Ratings and Cha	aracteristics <sup>b</sup>							
Reverse recovery time	t <sub>rr</sub>			-	59	-	ns	
Reverse recovery charge	Q <sub>rr</sub>	V <sub>DD</sub> = 32 V, I <sub>FM</sub> = 15 A, di/dt = 100 A/µs		-	nC			
Reverse recovery current	I <sub>RM</sub>	] "	, αι = 100 / γμο	-	2	3.2	Α	
Pulsed current <sup>a</sup>	I <sub>SM</sub>			-	-	719	Α	
Forward voltage	V <sub>SD</sub>	$I_F = 50 \text{ A}, V_{GS} = 0$		-	0.8	1.1	V	

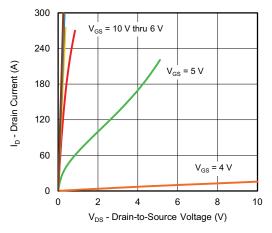
### Notes

- a. Pulse test; pulse width  $\leq$  300  $\mu$ s, duty cycle  $\leq$  2 %
- b. Guaranteed by design, not subject to production testing
- c. Independent of operating temperature

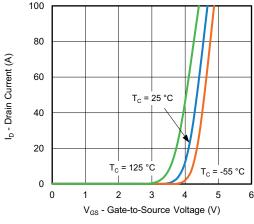
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



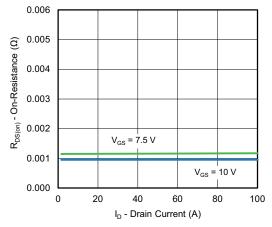
## **TYPICAL CHARACTERISTICS** (T<sub>A</sub> = 25 °C, unless otherwise noted)



#### **Output Characteristics**

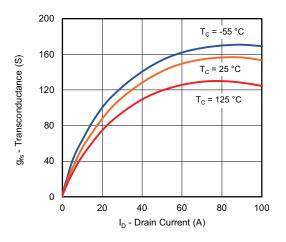


Transfer Characteristics

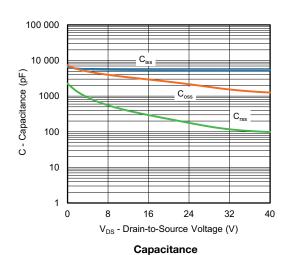


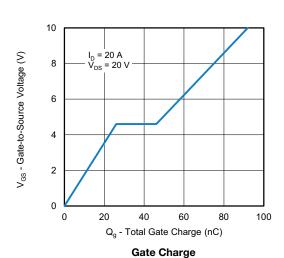
On-Resistance vs. Drain Current

S23-0430-Rev. B, 12-Jun-2023



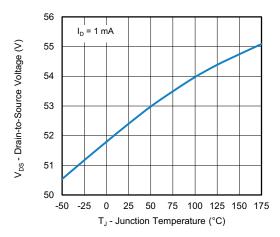
Transconductance



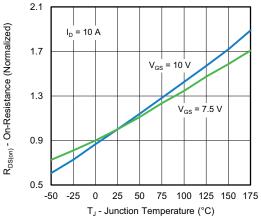




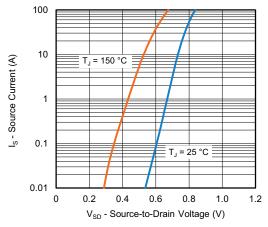
### **TYPICAL CHARACTERISTICS** (T<sub>A</sub> = 25 °C, unless otherwise noted)



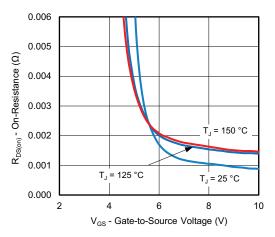
Drain Source Breakdown vs. Junction Temperature



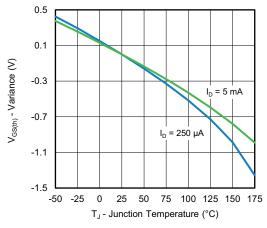
On-Resistance vs. Junction Temperature



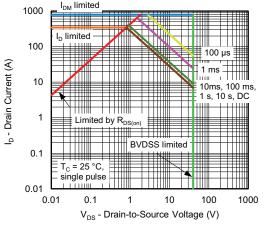
Source Drain Diode Forward Voltage



On-Resistance vs. Gate-to-Source Voltage



Threshold Voltage



Safe Operating Area

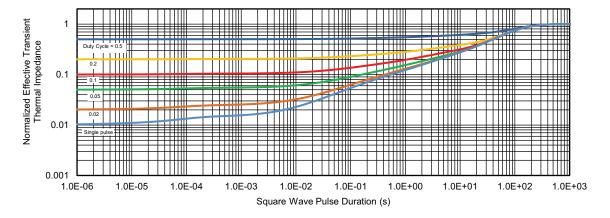
#### Note

a.  $V_{GS}$  > minimum  $V_{GS}$  at which  $R_{DS(on)}$  is specified

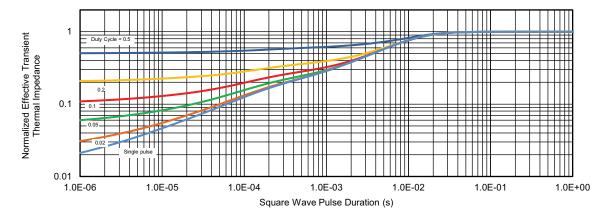
For technical questions, contact: automostech



### THERMAL RATINGS (T<sub>A</sub> = 25 °C, unless otherwise noted)



#### Normalized Thermal Transient Impedance, Junction-to-Ambient



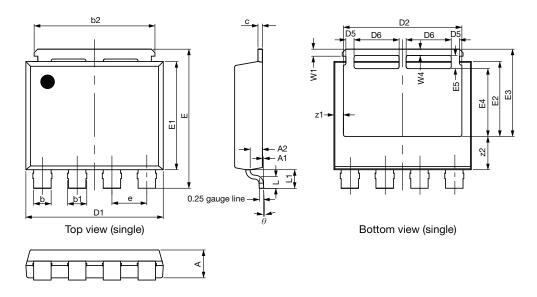
Normalized Thermal Transient Impedance, Junction-to-Case

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# PowerPAK® 8 x 8L BWL Case Outline 2



DIM	MILLIMETERS		INCHES			
DIM.	MIN.	NOM.	MAX.	MIN.	NOM.	MAX.
Α	1.50	1.60	1.70	0.059	0.063	0.067
A1	0.00	-	0.127	0.000	-	0.005
A2	0.655	0.705	0.755	0.026	0.028	0.030
b	0.92	1.00	1.08	0.036	0.039	0.043
b1	1.02	1.10	1.18	0.040	0.043	0.046
b2	6.84	6.94	7.04	0.269	0.273	0.277
С	0.20	0.25	0.30	0.008	0.010	0.012
D1	7.80	7.90	8.00	0.307	0.311	0.315
D2	6.70	6.80	6.90	0.264	0.268	0.272
D5	0.37	0.47	0.57	0.015	0.019	0.022
D6	2.49	2.59	2.69	0.098	0.102	0.106
е	1.97	2.00	2.03	0.078	0.079	0.080
E	7.90	8.00	8.10	0.311	0.315	0.319
E1	6.12	6.22	6.32	0.241	0.245	0.249
E2	4.21	4.31	4.41	0.166	0.170	0.174
E3	4.92	5.02	5.12	0.194	0.198	0.202
E4	3.80	3.90	4.00	0.150	0.154	0.157
E5	0.65	0.75	0.85	0.026	0.030	0.033
L	0.61	0.68	0.75	0.024	0.027	0.030
L1	1.00	1.07	1.15	0.039	0.042	0.045
W1	0.30	0.40	0.50	0.012	0.016	0.020
W4	0.32	0.37	0.42	0.013	0.015	0.017
z1	0.45	0.55	0.65	0.018	0.022	0.026
z2	1.81	1.91	2.01	0.071	0.075	0.079
θ	0°	-	5°	0°	-	5°

ECN: S19-0643-Rev. B, 05-Aug-2019

DWG: 6073

#### Note

Millimeter will govern

Revison: 05-Aug-2019 1 Document Number: 79736



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